ABSTRACT OF THE DISCLOSURE

First, a correction is made for correcting the mask pattern configuration of a photomask (3) used for exposure in accordance with the space between a mask pattern and an adjacent mask pattern thereto and a desired configuration to be transferred from the mask pattern. Second, a correction is made for dividing the photomask (3) into a plurality of mesh regions (M) to correct the pattern configuration of the photomask (3) in accordance with the occupation rate (R) of the mask pattern in each of the mesh regions (M).